

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	("20040227181").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/15 14:15
S2	0	("2004/0227181").URPN.	USPAT	OR	ON	2006/11/15 14:13
S3	0	Kyoung-Hwan adj Seoul.in.	USPAT	OR	ON	2006/11/15 14:14
S4	0	Kyoung adj Hwan adj Seoul.in.	USPAT	OR	ON	2006/11/15 14:14
S5	0	Kyoung adj Hwan adj Seoul.in.	US-PGPUB; USPAT	OR	ON	2006/11/15 14:14
S6	0	Kyoung-Hwan adj Seoul.in.	US-PGPUB; USPAT	OR	ON	2006/11/15 14:14
S7	1	Seoul.in.	US-PGPUB; USPAT	OR	ON	2006/11/15 14:14
S8	2	Multichannel adj (metal adj oxide adj semiconductor MOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/15 14:18
S9	4	Multi-channel adj (metal adj oxide adj semiconductor MOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/15 14:19
S10	4	Multi adj channel adj (metal adj oxide adj semiconductor MOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/15 14:19
S11	1	Multiple adj channel adj (metal adj oxide adj semiconductor MOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/15 14:54
S12	194	Multichannel same (metal adj oxide adj semiconductor MOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/15 15:07

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S13	60	S12 and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/15 15:10
S14	11	S12 and epitax\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/15 15:10
S15	83	dual adj channel with (mos mosfet CMOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:29
S16	23	S15 AND EPITAX\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:30
S17	72295	horizontal with channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:30
S18	4	S16 and S17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:32
S19	4	S18 and (source and drain and gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:36
S20	0	S19 and active	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:33

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S21	3423	active adj region near4 channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:33
S22	238	channel adj active adj region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:33
S23	1	S15 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:44
S24	8395	horizontal adj channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:47
S25	0	S15 and S24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:45
S26	194	Multichannel same (metal adj oxide adj semiconductor MOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:45
S27	1	S26 and S24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:45
S28	31448	horizontal near4 channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:46

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S29	3	S28 and S26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:46
S30	909	horizontal adj channel and (mos mosfet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:48
S31	0	S30 and S15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:48
S32	112	S30 and two adj channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:50
S33	10	S32 and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:54
S34	5340	double adj (gate gated)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:55
S35	10	S34 and S30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:55
S36	2	("20050104140").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/16 13:46
S37	0	("2005/0104140").URPN.	USPAT	OR	ON	2006/11/16 13:47

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S38	2	("7074657").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/16 13:47
S39	9	("20020115240" "20040063286" "20040262690" "20050023619" "5153688" "5500545" "6166412" "6864507" "6919250").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/11/16 13:48
S40	14	(US-20050112851-\$ or US-20060240622-\$ or US-20040227181-\$ or US-20050023619-\$ or US-20040262690-\$ or US-20020115240-\$).did. or (US-6236068-\$ or US-6097046-\$ or US-6919250-\$ or US-6166412-\$ or US-5500545-\$ or US-5153688-\$). did. or (JP-63140578-\$).did. or (US-20050104140-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2006/11/16 13:51
S41	10	S40 and epitax\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 13:52
S42	4	("5308782" "5372959" "5583362" "5965914").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/11/16 13:58
S43	0	S42 and mos	US-PGPUB; USPAT; USOCR	OR	ON	2006/11/16 13:59
S44	0	S42 and cmos	US-PGPUB; USPAT; USOCR	OR	ON	2006/11/16 13:59
S45	0	S42 and mosfet	US-PGPUB; USPAT; USOCR	OR	ON	2006/11/16 13:59
S46	2	S42 and epitax\$5	US-PGPUB; USPAT; USOCR	OR	ON	2006/11/16 15:08
S47	36629	source adj electrode	US-PGPUB; USPAT; USOCR	OR	ON	2006/11/16 15:08
S48	430	S47 and S34	USPAT	OR	ON	2006/11/16 15:10

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S49	1726	(438/197).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/17 10:34
S50	352	(438/157).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/17 10:37
S51	1861	vertical adj (source drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/17 10:38
S52	6	S49 and S51	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/17 10:38
S53	17	S49 and S50	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/17 10:38